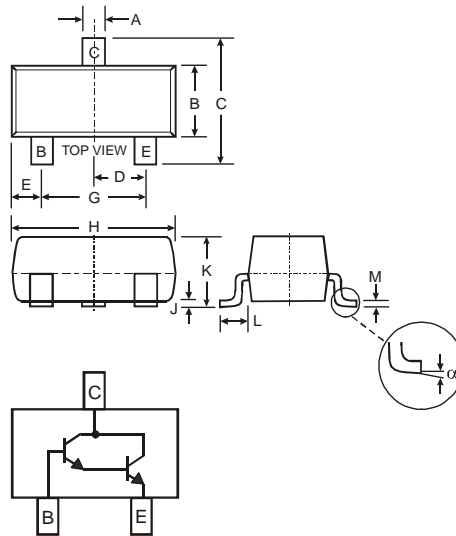


Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching
- High Current Gain
- **Lead, Halogen and Antimony Free, RoHS Compliant "Green" Device (Notes 3 and 4)**

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe).
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.008 grams (approximate)



SOT-23		
Dim	Min	Max
A	0.37	0.51
B	1.20	1.40
C	2.30	2.50
D	0.89	1.03
E	0.45	0.60
G	1.78	2.05
H	2.80	3.00
J	0.013	0.10
K	0.903	1.10
L	0.45	0.61
M	0.085	0.180
α	0°	8°
All Dimensions in mm		

Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	80	V
Collector-Emitter Voltage	V_{CEO}	80	V
Emitter-Base Voltage	V_{EBO}	12	V
Collector Current - Continuous	I_C	500	mA
Power Dissipation (Note 1)	P_D	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Operating and Storage and Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 2)					
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	80	—	V	$I_C = 100\mu\text{A}, I_E = 0$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	12	—	V	$I_E = 100\mu\text{A}, I_C = 0$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	80	—	V	$I_C = 100\mu\text{A}, I_B = 0$
Collector Cutoff Current	I_{CBO}	—	100	nA	$V_{CB} = 60\text{V}, I_E = 0$
	I_{CES}	—	500	nA	$V_{CE} = 10\text{V}$
Emitter Cutoff Current	I_{EBO}	—	100	nA	$V_{EB} = 10\text{V}, I_C = 0$
ON CHARACTERISTICS (Note 2)					
DC Current Gain	h_{FE}	10,000	—	—	$I_C = 10\text{mA}, V_{CE} = 5.0\text{V}$
		10,000	—	—	$I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	1.5	V	$I_C = 100\text{mA}, I_B = 100\mu\text{A}$
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	2.0	V	$I_C = 100\text{mA}, V_{CE} = 5.0\text{V}$
SMALL SIGNAL CHARACTERISTICS					
Output Capacitance	C_{obo}	8.0 Typical		pF	$V_{CB} = 10\text{V}, f = 1.0\text{MHz}, I_E = 0$
Input Capacitance	C_{ibo}	15 Typical		pF	$V_{EB} = 0.5\text{V}, f = 1.0\text{MHz}, I_C = 0$
Current Gain-Bandwidth Product	f_T	125	—	MHz	$V_{CE} = 5.0\text{V}, I_C = 10\text{mA}, f = 100\text{MHz}$

- Notes:
1. Device mounted on FR-4 PCB, 1.6x1.6x0.06 inch pad layout as shown on Diodes Inc. suggested pad layout document AP02001 which can be found on our website at <http://www.diodes.com/datasheets/ap02001.pdf>.
 2. Short duration pulse test used to minimize self-heating effect.
 3. No purposefully added lead. Halogen and Antimony Free.
 4. Product manufactured with Data Code V9 (week 33, 2008) and newer are built with Green Molding Compound. Product manufactured prior to Date Code V9 are built with Non-Green Molding Compound and may contain Halogens or Sb_2O_3 Fire Retardants.

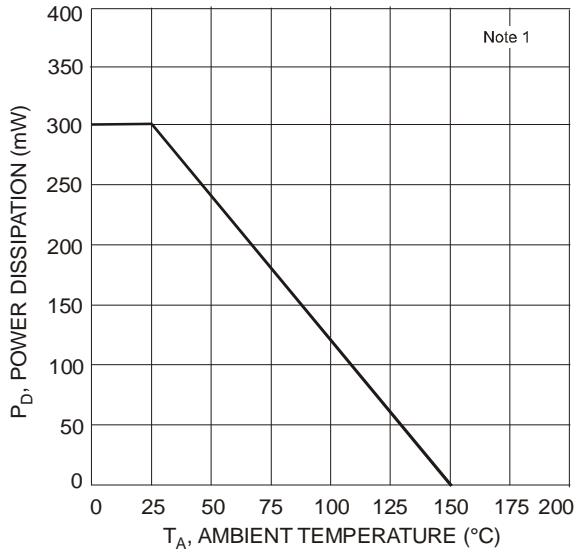


Fig. 1 Max Power Dissipation vs. Ambient Temperature

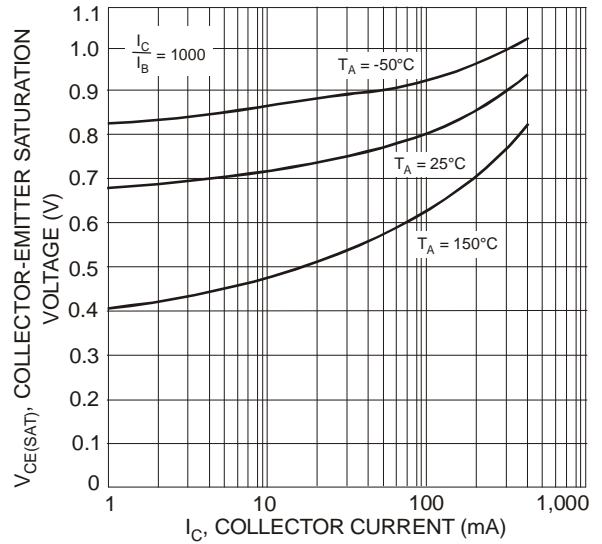


Fig. 2 Typical Collector-Emitter Saturation Voltage vs. Collector Current

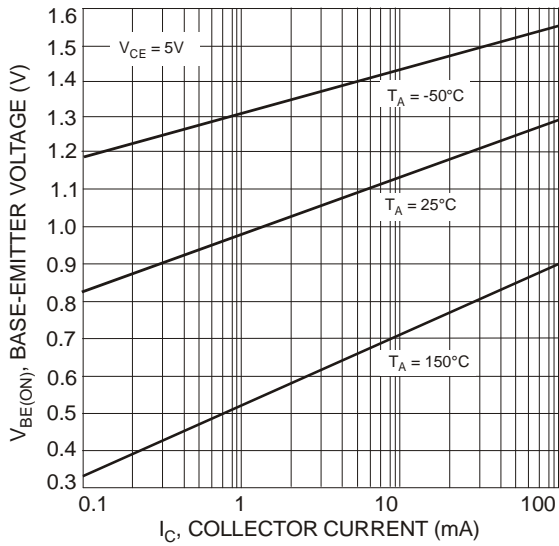


Fig. 3 Typical Base-Emitter Voltage vs. Collector Current

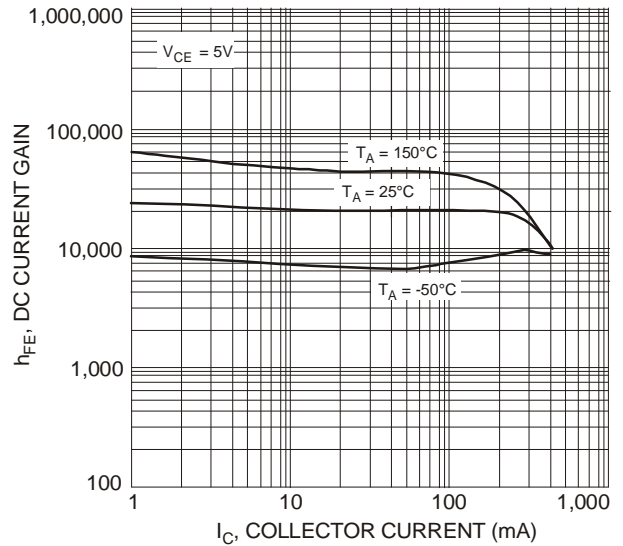


Fig. 4 Typical DC Current Gain vs. Collector Current

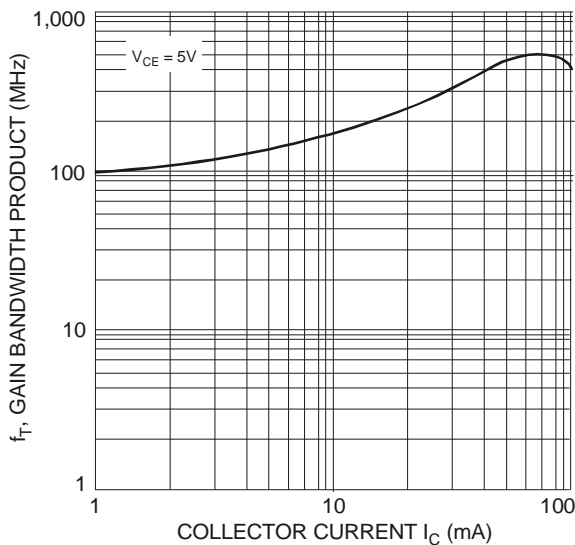


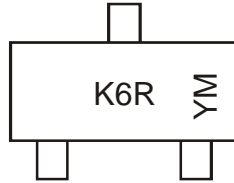
Fig. 5 Typical Gain Bandwidth Product vs. Collector Current

Ordering Information (Note 5)

Part Number	Packaging	Shipping
MMBTA28-7-F	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

Marking Information



K6R = Product Type Marking Code
 YM = Date Code Marking
 Y = Year ex: T = 2006
 M = Month ex: 9 = September

Date Code Key

Year	2006	2007	2008	2009	2010	2011	2012
Code	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [Darlington Transistors](#) category:

Click to view products by [Diodes Incorporated](#) manufacturer:

Other Similar products are found below :

[281287X](#) [SMMBT6427LT1G](#) [2N7371](#) [BDV64B](#) [JANTXV2N6287](#) [028710A](#) [SMMBTA64LT1G](#) [2N6350](#) [2SB1214-TL-E](#)
[SMMBTA14LT1G](#) [SBSP52T1G](#) [NJVMJD117T4G](#) [Jantx2N6058](#) [2N6353](#) [LB1205-L-E](#) [500-00005](#) [2N6053](#) [NJVMJD112G](#) [Jantx2N6352](#)
[Jantx2N6350](#) [BULN2803LVS](#) [ULN2001N](#) [2SB1383](#) [2SB1560](#) [2SB1647](#) [2SB852KT146B](#) [2SD2560](#) [TIP112TU](#) [TIP122TU](#) [BCV27](#)
[MMBTA13-TP](#) [MMBTA14-TP](#) [MMSTA28T146](#) [BSP50H6327XTSA1](#) [NTE2557](#) [NJVNJD35N04T4G](#) [MJD127T4](#) [FJB102TM](#)
[BCV26E6327HTSA1](#) [BCV46E6327HTSA1](#) [BSP61H6327XTSA1](#) [BU941ZPFI](#) [2SB1316TL](#) [2SD1980TL](#) [NTE2350](#) [NTE245](#) [NTE246](#)
[NTE2649](#) [NTE46](#) [NTE98](#)